

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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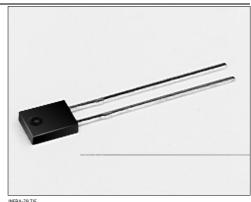




Silicon Photodiode

FEATURES

- Side-looking plastic package
- Linear response
- · Fast response time
- · Internal visible light rejection filter
- 50° (nominal) acceptance angle
- Mechanically and spectrally matched to SEP8506 and SEP8706 infrared emitting diodes



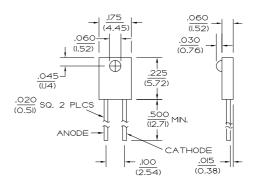
INFRA-79.TIF

DESCRIPTION

The SDP8276 is a PN silicon photodiode, transfer molded in a side-looking black plastic package, to minimize the effects of visible ambient light. The chip is positioned to accept radiant energy through a lens on the side of the package. The SDP8276 photodiode offers fast response time and a linear output. It is ideal for battery powered systems or anywhere power is at a premium.

OUTLINE DIMENSIONS in inches (mm)

3 plc decimals ±0.005(0.12) 2 plc decimals ±0.020(0.51)



DIM_074.cdr



Silicon Photodiode

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

| PARAMETER | SYMBOL | MIN | TYP | MAX | UNITS | TEST CONDITIONS |
|---------------------------|---------------------------------|-----|-----|-----|-------|-----------------------------------|
| Light Current | l _L | 4 | 7 | | μΑ | V _R =20 V |
| | | | | | | H=1 mW/cm ^{2 (1)} |
| Dark Current | ID | | | 50 | nA | H=0, V _R =20 VDC |
| Reverse Breakdown Voltage | V_{BR} | 50 | | | V | I _R =10 μA, H=0 |
| Angular Response (2) | Ø | | 50 | | degr. | I _F =Constant |
| Rise And Fall Time | t _r , t _f | | 50 | | ns | $V_R=20 \text{ V}, R_L=50 \Omega$ |

- Notes

 1. The radiation source is an IRED with a peak wavelength of 935 nm.

 2. Angular response is defined as the total included angle between the half sensitivity points.

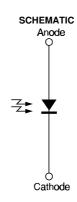
ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Operating Temperature Range -40 to +85°C -40 to +85°C Storage Temperature Range Soldering Temperature (5 sec) 240°C Cathode Anode Voltage 50 V Power Dissipation 100 mW (1)

Notes

1. Derate linearly from 25°C free-air temperature at the rate of 0.78 mW/°C.



Honeywell reserves the right to make changes in order to improve design and supply the best products possible. Honeywell

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SWITCHING TIME TEST CIRCUIT

GaAs Emitter

H

Anode

Figure 6

F

SWITCHING WAVEFORM

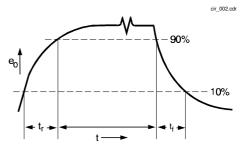


Fig. 1 Responsivity vs Angular Displacement

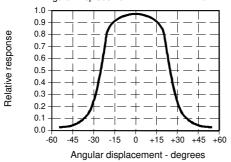


Fig. 2 Dark Current vs

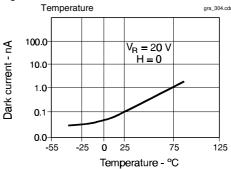
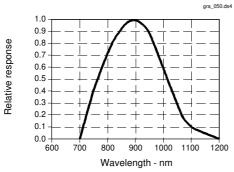


Fig. 3 Spectral Responsivity



All Performance Curves Show Typical Values

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